Sheet <u>1</u> of <u>1</u> FORM PTO-1449 PARTMENT OF COMMERCE ATTY, DOCKET NO. APPLICATION NO. (REV.7-80) PATENT AND TRADEMARK OFFICE 501082.06 (98-0616.05) 09/652.842 APPLICANT(S) INFORMATION DISCLOSURE STATEMENT Vishnu K. Agarwal Use several sheets if necesCOPY OF PAPERS FILING DATE **GROUP ART UNIT** ORIGINALLY FILED August 31, 2000 2825 JAN 2 4 2002 **U.S. PATENT DOCUMENTS** EXAMPLE INITIAL & DOCUMENT NUMBER SUBCLASS DATE NAME **CLASS** FILING DATE IF APPROPRIATE 235 13/4 3,649,886 03/14/72 Kooi 317 53.1 427 pr-01/05/88 Yamazaki ΑB 4,717,602 437 190 Bu 08/03/93 5,232,871 Ho AC 437 190 5,552,339 09/03/96 Hsieh ΑD 592 438 03/31/98 ΑE 5.733.816 Iyer et al. 438 627 6.136.690 10/24/00 Li ΑF 11/28/00 Jain et al. 438 681 AG | 6,153,519 Bu Narwankar et al. 438 785 ан 6,204,203 03/20/01 6,245,662 06/12/01 Naik et al. 438 622 ΑI FOREIGN PATENT DOCUMENTS CLASS SUBCLASS TRANSLATION DOCUMENT NUMBER DATE COUNTRY YES X JP (Abstract only) ΑJ 355011329 A 01/26/80 X 410070091 A 03/10/98 JP (Abstract only) ΑK OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.) Anonymous, "Oxide-Free Dielectric/GaAs Interface With No Excess As", IBM Technical Disclosure Bulletin, Vol. 33, No. 11, April 1, 1991, p. 352. ΑL

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EXAMINER By Kessen DATE CONSIDERED 04/02

\* EXAMINER: Initial if reference considered, whether or notcriteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applican(s).